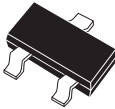


CMPT2369

NPN SILICON TRANSISTOR



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT2369 type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for ultra high speed switching applications.

Marking Code is C1J.

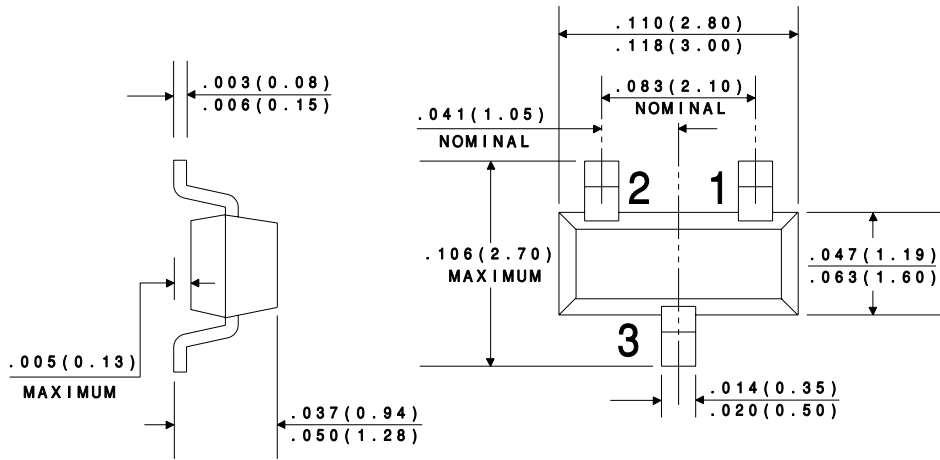
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CB0}	40	V
Collector-Emitter Voltage	V_{CES}	40	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	4.5	V
Collector Current	I_C	500	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	357	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=20\text{V}$		0.4	μA
I_{CBO}	$V_{CB}=20\text{V}, T_A=125^{\circ}\text{C}$		30	μA
BV_{CB0}	$I_C=10\mu\text{A}$	40		V
BV_{CES}	$I_C=10\mu\text{A}$	40		V
BV_{CEO}	$I_C=10\text{mA}$	15		V
BV_{EBO}	$I_E=10\mu\text{A}$	4.5		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.25	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.7	0.85	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	40	120	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=100\text{mA}$	20		
C_{ob}	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$		4.0	pF
f_T	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	500		MHz
t_s	$V_{CC}=3.0\text{V}, I_C=I_{B1}=I_{B2}=10\text{mA}$		13	ns
t_{on}	$V_{CC}=3.0\text{V}, I_C=10\text{mA}, I_{B1}=3.0\text{mA}$		12	ns
t_{off}	$V_{CC}=3.0\text{V}, I_C=10\text{mA}, I_{B1}=3.0\text{mA}, I_{B2}=1.5\text{mA}$		18	ns

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR